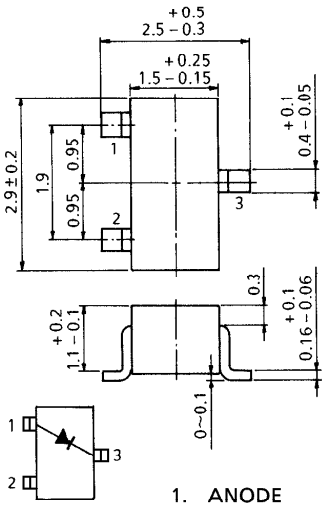
TOSHIBA DIODE SILICON EPITAXIAL PLANAR TYPE

1SS250

HIGH SPEED SWITCHING APPLICATIONS.

Unit in mm

- Low Forward Voltage : $V_F(2) = 0.90V$ (Typ.)
- Fast Reverse Recovery Time : $t_{rr} = 60ns$ (Max.)
- Small Total Capacitance : $C_T = 1.5pF$ (Typ.)
- Small Package : SC-59



S-MINI	
JEDEC	TO-236MOD
EIAJ	SC-59
TOSHIBA	1-3G1B

Weight : 0.012g

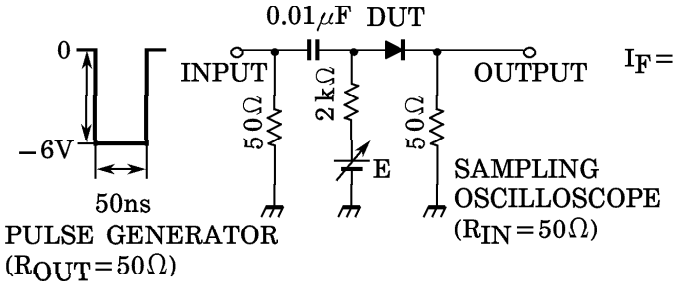
MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Peak Reverse Voltage	V_{RM}	250	V
Reverse Voltage	V_R	200	V
Peak Forward Current	I_{FM}	300	mA
Average Forward Current	I_O	100	mA
Surge Current (10ms)	I_{FSM}	2	A
Power Dissipation	P	150	mW
Junction Temperature	T_j	125	°C
Storage Temperature Range	T_{stg}	−55~125	°C

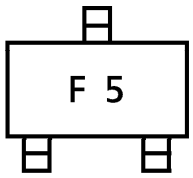
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Forward Voltage	$V_{F(1)}$	$I_F = 10mA$	—	0.72	1.00	V
	$V_{F(2)}$	$I_F = 100mA$	—	0.90	1.20	
Reverse Current	$I_{R(1)}$	$V_R = 50V$	—	—	0.1	μA
	$I_{R(2)}$	$V_R = 200V$	—	—	1.0	
Total Capacitance	C_T	$V_R = 0$, f = 1MHz	—	1.5	3.0	pF
Reverse Recovery Time	t_{rr}	$I_F = 10mA$ (Fig.1)	—	10	60	ns

Fig1. REVERSE RECOVERY TIME (t_{rr}) TEST CIRCUIT



MARKING



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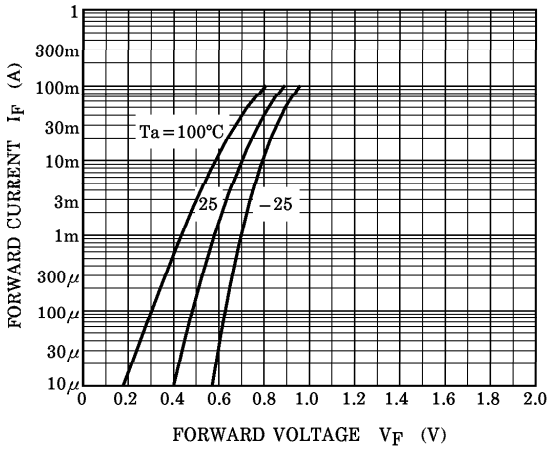
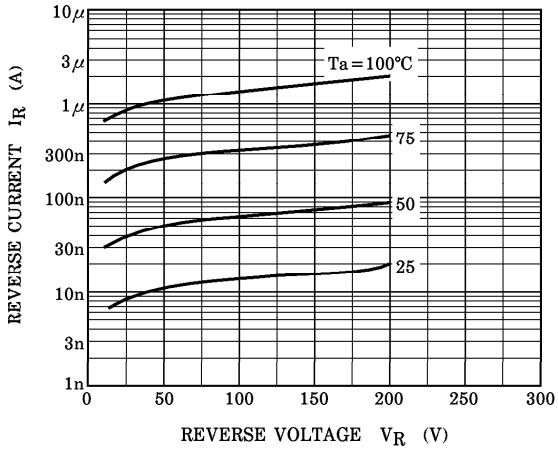
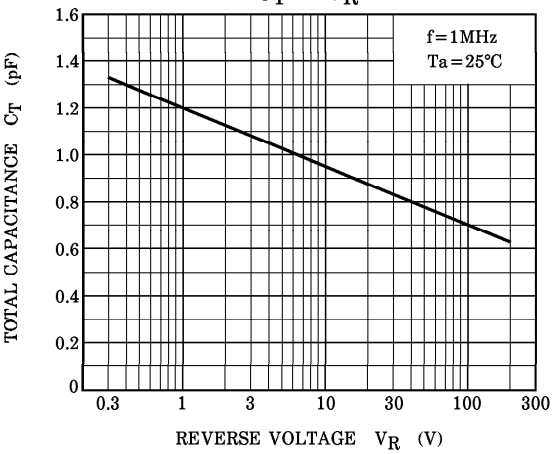
$I_F - V_F$



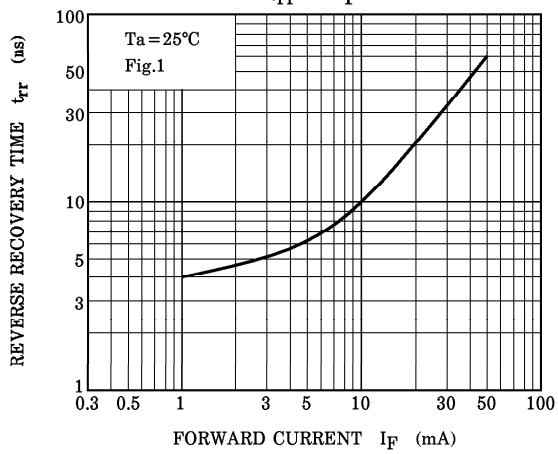
$I_R - V_R$



$C_T - V_R$



$t_{rr} - I_F$



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